Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Ultra thin package profile of 0.37 mm

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-1	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -1 A; T_j = 25 °C		-	430	510	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa259

6. Ordering information

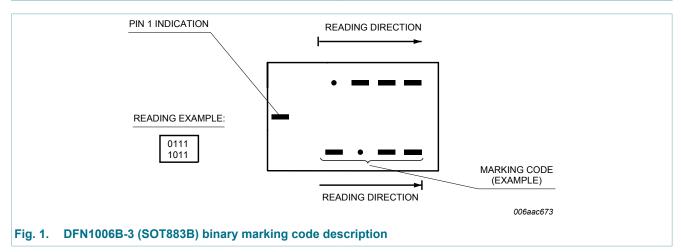
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMZB320UPE	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZB320UPE	0101 0010



8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-1	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-0.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	760	mW
		T _{sp} = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode		'		'	
Is	source current	T _{amb} = 25 °C	[1]	-	-0.7	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

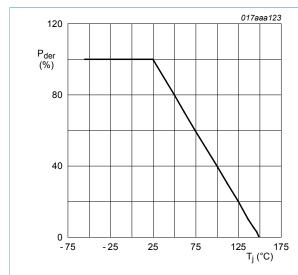


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

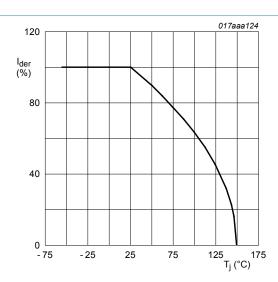


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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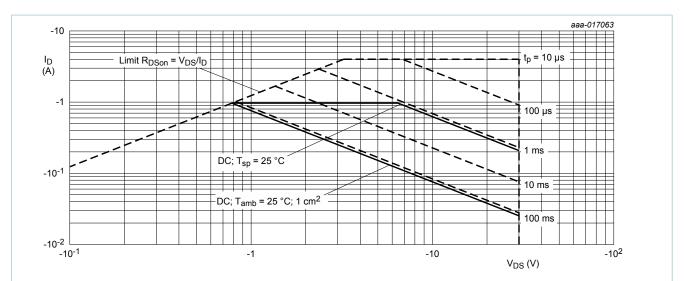


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fro	thermal resistance		[1]	-	315	360	K/W
	from junction to ambient		<u>[2]</u>	-	145	165	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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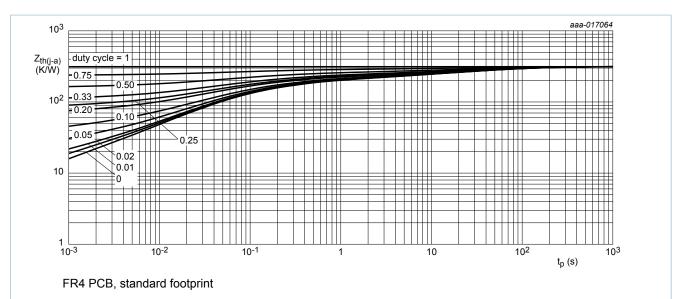


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

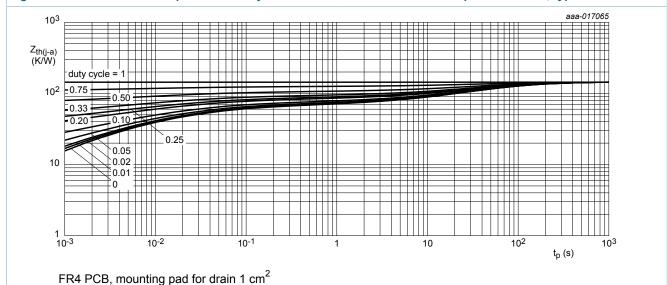


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	430	510	mΩ
resi		V _{GS} = -4.5 V; I _D = -1 A; T _j = 150 °C	-	680	810	mΩ
		V _{GS} = -2.5 V; I _D = -0.8 A; T _j = 25 °C	-	570	770	mΩ
		V _{GS} = -1.8 V; I _D = -0.25 A; T _j = 25 °C	-	750	1140	mΩ
		V _{GS} = -1.5 V; I _D = -0.01 A; T _j = 25 °C	-	950	1610	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -1 A; T_{j} = 25 °C	-	2.1	-	S
Dynamic ch	naracteristics		'			,
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -1 A; V_{GS} = -4.5 V;	-	1.4	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.3	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	122	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	11	-	pF
C _{rss}	reverse transfer capacitance		-	9	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I_{D} = -1 A; V_{GS} = -4.5 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	6	-	ns
t _{d(off)}	turn-off delay time		-	22	-	ns
t _f	fall time		-	5	-	ns
Source-drai	in diode		I	1	1	1
V_{SD}	source-drain voltage	$I_S = -0.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-1	-1.2	V
						1

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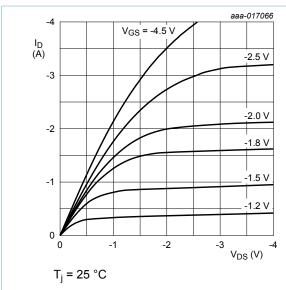
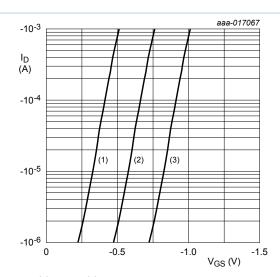


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values



 $V_{DS} = -5 V$ $T_i = 25 °C$

(1) minimum values

(2) typical values

(3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage

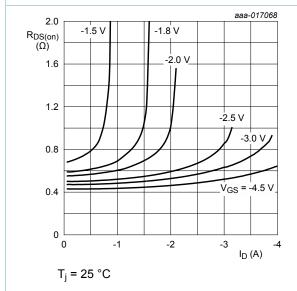


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

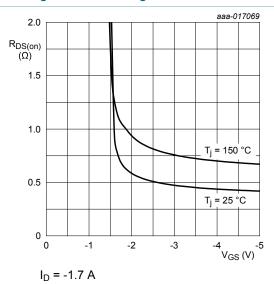


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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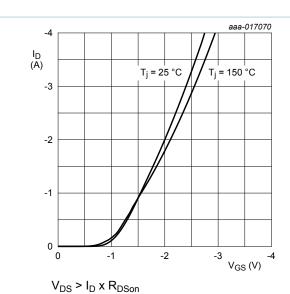


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

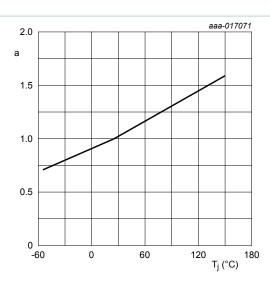
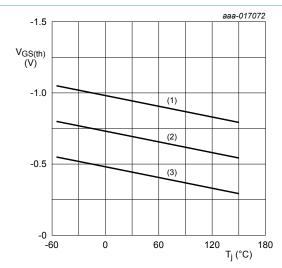


Fig. 12. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

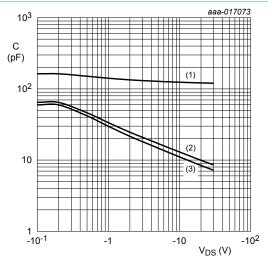
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = -250 \mu A; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) maximum values

Fig. 13. Gate-source threshold voltage as a function of ambient temperature



f = 1 MHz; V_{GS} = 0 V

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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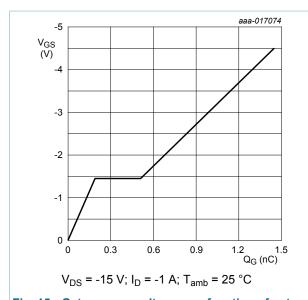


Fig. 15. Gate-source voltage as a function of gate charge; typical values

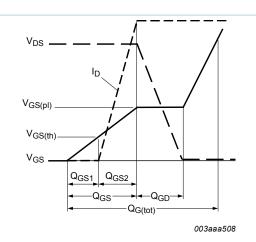


Fig. 16. Gate charge waveform definitions

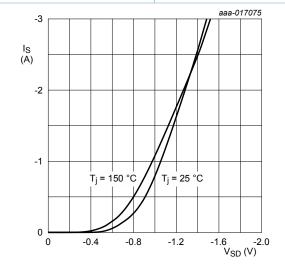
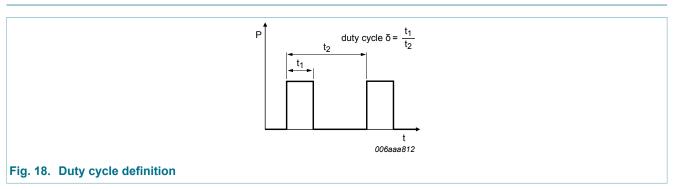


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



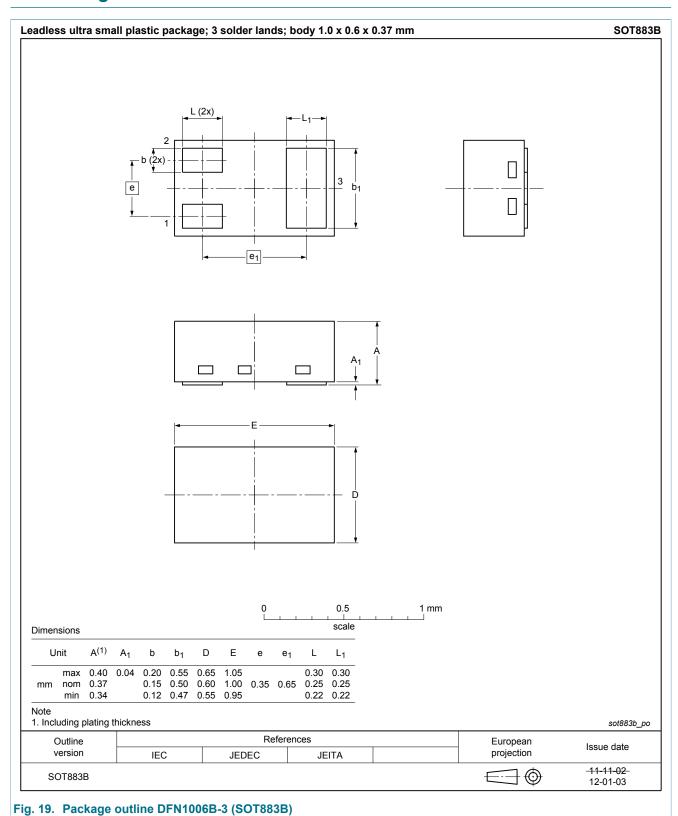
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12. Package outline

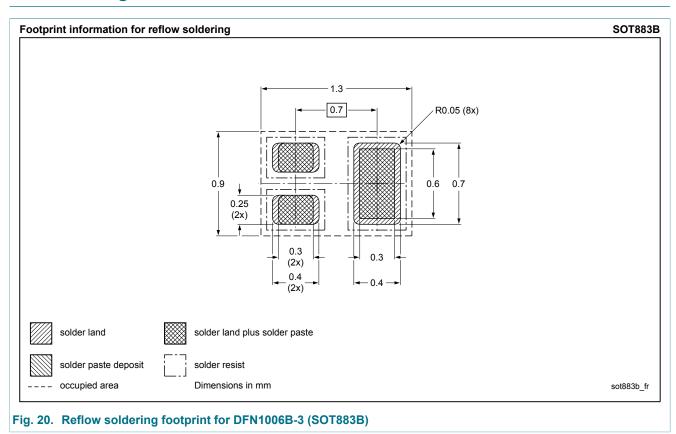


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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB320UPE v.1	20150324	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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